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SHEET 1 OF 1

INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449)				ATTY. DOCKET NO. 071971-0388	SERIAL NO. Not yet assigned 10/553628	
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U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code ₂ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
Mbh	US	2003/0080384 A1			Corresponds to JP 2003-234301 A	
Mbh	US	5977564 A			Corresponds to JP 10-321854 A	
Mbh	US	6097039 A			Corresponds to JP 2001-517375 A	
	US					
	US					
	US					
	US					
	US					
FOREIGN PATENT DOCUMENTS						
EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes-Number-Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Figures Appear	Translation Yes No
Mbh		JP 2003-234301 A	08-22-2003	Matsushita Electric Industrial Co., Ltd.	Corresponds to US 2003/0080384 A1	
Mbh		JP 2003-209251 A	07-25-03	Japan Atomic Energy Research Institute		
Mbh		JP 10-321854 A	12-04-1998	Toshiba Corp.	Corresponds to US 5977564 A	
Mbh		JP 2000-294777 A	10-20-2000	Mitsubishi Electric Corp.		
Mbh		JP 2001-517375 A	10-02-2001	Siemens AG.	Corresponds to US 6097039 A	
Mbh		JP 2001-144288 A	05-25-2001	Denso Corp.		
Mbh		JP 2002-280381 A	09-27-2002	Fuji Electric Co., Ltd.		
Mbh		WO 99/48153	09-23-1999	HITACHI, LTD.		JAPAN (w/English Abstract)
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)						
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.				
Mbh		G.Y. CHUNG, et al., "Improved Invention Channel Mobility for 4H-SiC MOSFETs Following High Temperature Anneals in Nitric Oxide," Electron Device Letters, April 2001, pp 176-178, Vol 22, No. 4, IEEE				
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